Isolated Compact IGBT Gate Driver with DESAT

NCD57084, NCV57084

NCx57084 is a high current single channel IGBT gate driver with 2.5 kVrms internal galvanic isolation designed for high system efficiency and reliability in high power applications. The driver includes DESAT short circuit protection with soft turn off and fault reporting in a narrow body SOIC−8 package. NCx57084 accommodates wide range of input bias voltage and signal levels from 3.3 V to 20 V, and wide range of output bias voltage up to 30 V.

Features

- High Peak Output Current (+7A/−7 A)
- Low Output Impedance for Enhanced IGBT Driving
- Short Propagation Delays with Accurate Matching
- DESAT Protection with Programmable Delay
- Negative Voltage (Down to −9 V) Capability for DESAT
- IGBT Gate Clamping during Short Circuit
- IGBT Gate Active Pull Down
- Soft Turn Off During IGBT Short Circuit
- Tight UVLO Thresholds for Bias Flexibility
- Output Partial Pulse Avoidance During UVLO/DESAT (Restart)
- 3.3 V, 5 V, and 15 V Logic Input
- 2.5 kVrms Galvanic Isolation
- High Transient Immunity
- High Electromagnetic Immunity
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- This Device is Pb−Free, Halogen Free/BFR Free and is RoHS Compliant

Typical Applications

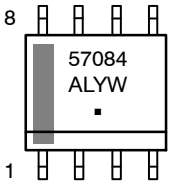
- Motor Control
- Automotive Applications
- Uninterruptible Power Supplies (UPS)
- Industrial Power Supplies
- HVAC
- Industrial Pumps and Fans

ON Semiconductor®

www.onsemi.com

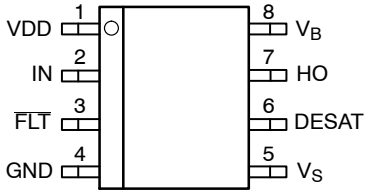
SOIC−8 NB
CASE 751−07

MARKING DIAGRAM



57084	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
▪	= Pb−Free Package

PIN CONNECTIONS



NCx57084
x = D or V

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

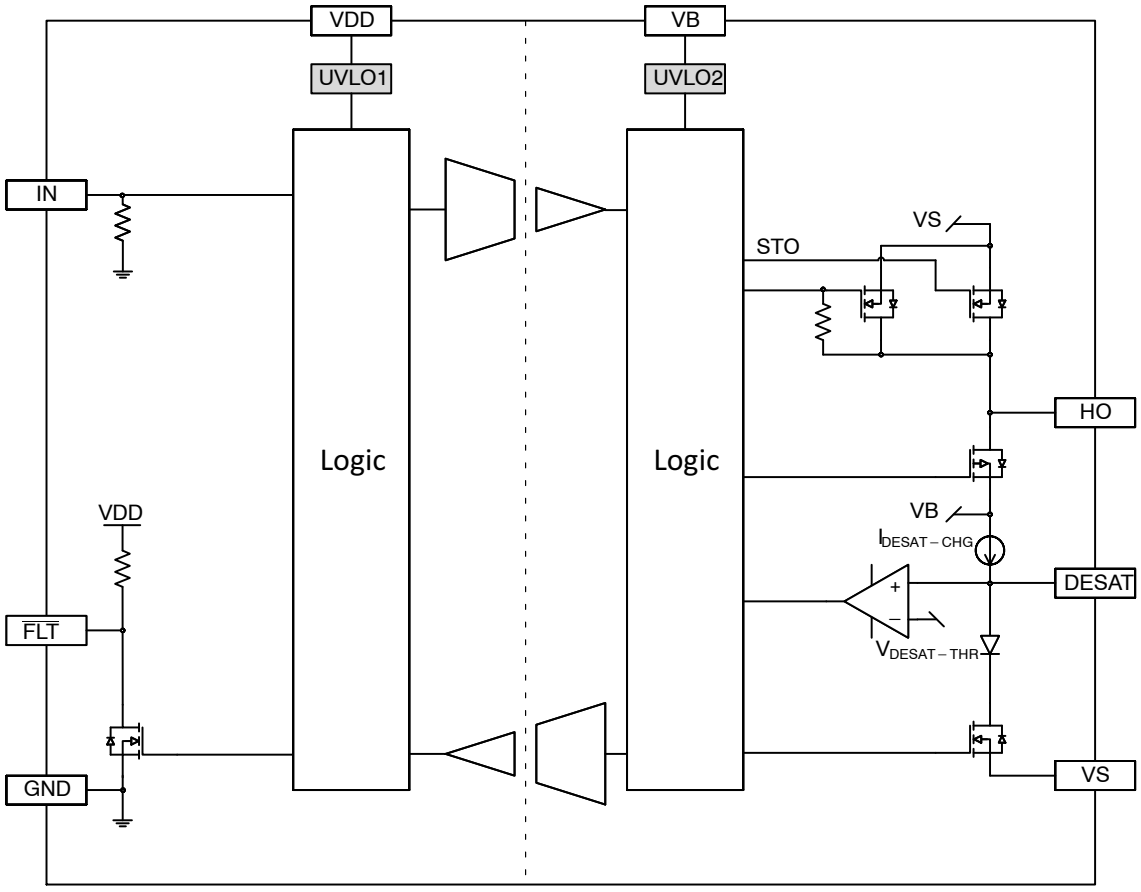


Figure 1. Simplified Block Diagram

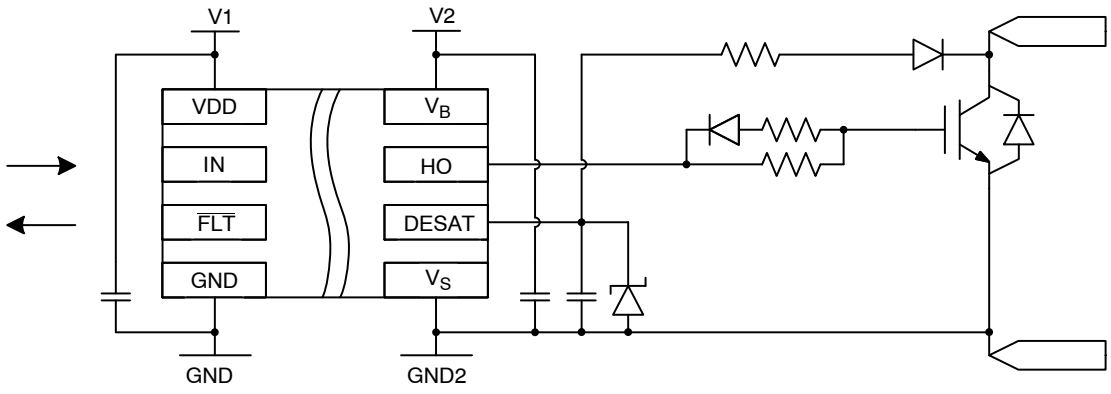


Figure 2. Simplified Application Schematics

FUNCTION DESCRIPTION

Pin Name	No.	I/O	Description
V_{DD}	1	Power	Input side power supply. A good quality bypassing capacitor is required from this pin to GND and should be placed close to the pins for best results. The under voltage lockout (UVLO1) circuit enables the device to operate at power on when a typical supply voltage higher than $V_{UVLO1-OUT-ON}$ is present. Please see Figure 4 for more details.
IN	2	I	Non−inverted gate driver input. It is internally clamped to GND and has an equivalent pull−down resistor of 100 kΩ to ensure that output is low in the absence of an input signal.
$\overline{FLT}$	3	O	Fault output (active low) that allows communication to the main controller that the driver has encountered a desaturation, or UVLO1, or UVLO2 condition and has deactivated the output. There is an internal 50 kΩ pull−up resistor connected to this pin. Multiple of them from different drivers can be “OR”ed together. $\overline{FLT}$ and HO will go high automatically after t_{MUTE} expires along with a rising edge of IN to avoid partial output pulse on HO. This is a feature called “Re−start”.
GND	4	Power	Input side ground reference.
V_S	5	Power	Output side ground reference.
DESAT	6	I/O	Input for detecting the desaturation of IGBT due to a short circuit condition. An internal constant current source $I_{DESAT-CHG}$ charging an external capacitor connected to this pin allows a programmable blanking delay every ON cycle before DESAT fault is processed, thus preventing false triggering. When the DESAT voltage goes up and reaches $V_{DESAT-THR}$, the output is driven low. Further, the $\overline{FLT}$ output is activated, please refer to Figure 6. $\overline{FLT}$ and HO will be kept low (including soft turn off time) at least for a period defined by t_{MUTE}.
HO	7	O	Driver output that provides the appropriate drive voltage and source/sink current to the IGBT/FET gate. HO is actively pulled low during start−up.
V_B	8	Power	Output side positive power supply. The operating range for this pin is from UVLO2 to its maximum allowed value. A good quality bypassing capacitor is required from this pin to V_S and should be placed close to the pins for best results. The under voltage lockout (UVLO2) circuit enables the device to operate at power on when a typical supply voltage higher than $V_{UVLO2-OUT-ON}$ is present. Please see Figure 5 for more details.

SAFETY AND INSULATION RATINGS

Symbol	Parameter		Value	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1 Rated Mains Voltage	< 150 V_{RMS}	I–IV	
		< 300 V_{RMS}	I–IV	
		< 450 V_{RMS}	I–IV	
		< 600 V_{RMS}	I–IV	
		< 1000 V_{RMS}	I–III	
	Climatic Classification		40/100/21	
	Pollution Degree (DIN VDE 0110/1.89)		2	
CTI	Comparative Tracking Index (DIN IEC 112/VDE 0303 Part 1)		600	
V_{PR}	Input–to–Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC		2250	V_{PK}
V_{IORM}	Maximum Repetitive Peak Voltage		1200	V_{PK}
V_{IOWM}	Maximum Working Insulation Voltage		870	V_{RMS}
V_{IOTM}	Highest Allowable Over Voltage		4200	V_{PK}
E_{CR}	External Creepage		4.0	mm
E_{CL}	External Clearance		4.0	mm
DTI	Insulation Thickness		8.65	μm
T_{Case}	Safety Limit Values – Maximum Values in Failure; Case Temperature		150	°C
$P_{S,INPUT}$	Safety Limit Values – Maximum Values in Failure; Input Power		132	mW
$P_{S,OUTPUT}$	Safety Limit Values – Maximum Values in Failure; Output Power		1128	mW
R_{IO}	Insulation Resistance at TS, V_{IO} = 500 V		10^9	Ω

ISOLATION CHARACTERISTICS

Symbol	Parameter	Conditions	Value	Unit
V_{ISO}, INPUT– OUTPUT	Input–Output Isolation Voltage	T_A = 25°C, Relative Humidity < 50%, t = 1.0 minute, I_{I-O} < 30 μA, 50 Hz (Notes 1, 2, 3)	2500	V_{RMS}
R_{ISO}	Isolation Resistance	V_{I-O} = 500 V (Note 1)	10^{11}	Ω

1. Device is considered a two–terminal device: pins 1 to 4 are shorted together and pins 5 to 8 are shorted together.
2. 2,500 VRMS for 1–minute duration is equivalent to 3,000 VRMS for 1–second duration.
3. The input–output isolation voltage is a dielectric voltage rating per UL1577. It should not be regarded as an input–output continuous voltage rating. For the continuous working voltage rating, refer to equipment–level safety specification or DIN VDE V 0884–11 Safety and Insulation Ratings Table.

ABSOLUTE MAXIMUM RATINGS (Note 4) Over operating free−air temperature range unless otherwise noted.

Symbol	Parameter	Minimum	Maximum	Unit
V_{DD} − GND	Supply Voltage, Input Side	−0.3	22	V
V_B − V_S	Supply Voltage, Output Side	−0.3	32	V
V_{HO} − V_S	Gate−driver Output Voltage	−0.3	V_{BS} + 0.3	V
I_{PK-SRC}	Gate−driver Output Sourcing Peak Current (maximum pulse width = 10 μs, maximum duty cycle = 0.2%, V_D − V_S = 15 V)	−	7	A
I_{PK-SNK}	Gate−driver Output Sinking Peak Current (maximum pulse width = 10 μs, maximum duty cycle = 0.2%, V_D − V_S = 15 V)	−	7.5	A
V_{IN} − GND	Voltage at IN, $\overline{FLT}$	−0.3	V_{DD} + 0.3	V
I_{FLT}	Output current of $\overline{FLT}$	−	10	mA
V_{DESAT} − V_S	Voltage at DESAT (Note 5)	−9	V_{BS} + 0.3	V
PD	Power Dissipation (Note 6)	−	1123	mW
ESD_{HBM}	ESD Capability, Human Body Model (Note 7)	−	±2	kV
ESD_{CDM}	ESD Capability, Charged Device Model (Note 7)	−	±2	kV
MSL	Moisture Sensitivity Level	−	1	−
T_J(max)	Maximum Junction Temperature	−40	150	°C
T_{STG}	Storage Temperature Range	−65	150	°C
T_{SLD}	Lead Temperature Soldering Reflow, Pb−Free (Note 8)	−	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

4. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
5. The minimum value is verified by characterization with a single pulse of 1.5 mA for 300 μs.
6. The value is estimated for ambient temperature 25°C and junction temperature 150°C, 650 mm², 1 oz copper, 2 surface layers and 2 internal power plane layers. Power dissipation is affected by the PCB design and ambient temperature.
7. This device series incorporates ESD protection and is tested by the following methods:
   ESD Human Body Model tested per AEC−Q100−002 (EIA/JESD22−A114).
   ESD Charged Device Model tested per AEC−Q100−011 (EIA/JESD22−C101).
   Latchup Current Maximum Rating: ≤100 mA per JEDEC standard: JESD78, 125°C.
8. For information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS (Note 9, 10)

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction−to−Air	100 mm², 1 oz Copper, 1 Surface Layer	179	°C/W
		100 mm², 1 oz Copper, 2 Surface Layers and 2 Internal Power Plane Layers	110	

9. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
10. Values based on copper area of 100 mm² (or 0.16 in²) of 1 oz copper thickness and FR4 PCB substrate.

OPERATING RANGES (Note 11)

Symbol	Parameter	Min	Max	Unit
V_{DD}−GND	Supply Voltage, Input Side	UVLO1	20	V
V_B−V_S	Supply Voltage, Output Side	UVLO2	30	V
V_{IN}	Logic Input Voltage at IN	GND	V_{DD}	V
$\lvert dV_{ISO}/dt \rvert$	Common Mode Transient Immunity	100	−	kV/μs
T_A	Ambient Temperature	−40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

11. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

ELECTRICAL CHARACTERISTICS V_{DD} = 5 V, V_{BS} = 15 V.
For typical values T_A = 25°C, for min/max values, T_A is the operating ambient temperature range that applies, unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
VOLTAGE SUPPLY						
$V_{UVLO1-OUT-ON}$	UVLO1 Output Enabled		–	–	3.1	V
$V_{UVLO1-OUT-OFF}$	UVLO1 Output Disabled		2.4	–	–	V
$V_{UVLO1-HYST}$	UVLO1 Hysteresis		0.1	–	–	V
$V_{UVLO2-OUT-ON}$	UVLO2 Output Enabled		12.4	12.9	13.4	V
$V_{UVLO2-OUT-OFF}$	UVLO2 Output Disabled		11.5	12	12.5	V
$V_{UVLO2-HYST}$	UVLO2 Hysteresis		0.7	1	–	V
$I_{DD-0-3.3}$	Input Supply Quiescent Current	IN = Low, V_{DD} = 3.3 V, $\overline{FLT}$ = Hig	–	–	2	mA
I_{DD-0-5}		IN = Low, V_{DD} = 5 V, $\overline{FLT}$ = High	–	–	2	mA
$I_{DD-0-15}$		IN = Low, V_{DD} = 15 V, $\overline{FLT}$ = High	–	–	2	mA
$I_{DD-100-5}$		IN = High, V_{DD} = 5 V, $\overline{FLT}$ = High	–	–	6	mA
I_{BS-0}	Output Supply Quiescent Current	IN = Low, no load	–	–	4	mA
I_{BS-100}		IN = High, no load	–	–	6	mA
LOGIC INPUT AND OUTPUT						
V_{IL}	Low Input Voltage (Note 12)				$0.3 \times V_{DD}$	V
V_{IH}	High Input Voltage (Note 12)		$0.7 \times V_{DD}$			V
$V_{IN-HYST}$	Input Hysteresis Voltage (Note 12)			$0.15 \times V_{DD}$		V
I_{IN}	Input Current	V_{IN} = V_{DD}		50		μA
I_{FLT-L}	$\overline{FLT}$ Pull−up Current (50 kΩ pull−up resistor)	V_{FLT} = Low	–	100	–	μA
V_{FLT-L}	$\overline{FLT}$ Low Level Output Voltage	I_{FLT} = 5 mA	–	–	0.3	V
t_{MIN1}	Input Pulse Width of IN for No Response at Output		–	–	10	ns
t_{MIN2}	Input Pulse Width of IN for Guaranteed Response at Output		40	–	–	ns
DRIVER OUTPUT						
V_{HOL1}	Output Low State ($V_{HO} - V_S$)	I_{SNK} = 200 mA	–	0.1	0.22	V
V_{HOL2}		I_{SNK} = 1.0 A, T_A = 25°C	–	0.4	1	
V_{HOH1}	Output High State ($V_B - V_{HO}$)	I_{SRC} = 200 mA	–	0.2	0.35	V
V_{HOH2}		I_{SRC} = 1.0 A, T_A = 25°C	–	0.6	1.7	
$I_{PK-SNK1}$	Peak Driver Current, Sink (Note 13)		–	7.5	–	A
$I_{PK-SNK2}$	Peak Driver Current, Sink (Note 13)	V_{HO} = 9 V (near IGBT Miller Plateau)	–	7	–	A
$I_{PK-SRC1}$	Peak Driver Current, Source (Note 13)		–	7	–	A
$I_{PK-SRC2}$	Peak Driver Current, Source (Note 13)	V_{HO} = 9 V (near IGBT Miller Plateau)	–	5	–	A
DESAT PROTECTION						
$V_{DESAT-THR}$	DESAT Threshold Voltage		8.4	9	9.5	V
$V_{DESAT-NEG}$	DESAT Negative Voltage	I_{DESAT} = 1.5 mA	–	−8	–	V
$I_{DESAT-CHG}$	Blanking Charge Current	V_{DESAT} = 7 V	0.45	0.5	0.55	mA
$I_{DESAT-DIS}$	Blanking Discharge Current		–	50	–	mA

ELECTRICAL CHARACTERISTICS (continued) V_{DD} = 5 V, V_{BS} = 15 V.
For typical values T_A = 25°C, for min/max values, T_A is the operating ambient temperature range that applies, unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
IGBT SHORT CIRCUIT CLAMPING						
V_{CLP-HO}	IGBT Short Circuit Clamping (V_{HO} − V_B)	IN = High, I_{HO} = 500 mA, t_{CLP} = 10 μs	–	0.7	1.5	V
DYNAMIC CHARACTERISTICS						
t_{PD-ON}	IN to HO High Propagation Delay	C_{LOAD} = 10 nF V_{IH} to 10% of HO Change for PW > 150 ns	40	60	90	ns
t_{PD-OFF}	IN to HO Low Propagation Delay	C_{LOAD} = 10 nF V_{IL} to 90% of HO Change for PW > 150 ns	40	60	90	ns
$t_{DISTORT}$	Propagation Delay Distortion (= t_{PD-ON} − t_{PD-OFF})	T_A = 25°C, PW > 150 ns	–	0	–	ns
		T_A = −40°C to 125°C, PW > 150 ns	−25	–	25	
$t_{DISTORT\_TOT}$	Prop Delay Distortion between Parts	PW > 150 ns	−30	0	30	ns
t_{RISE}	Rise Time (see Figure 3) (Note 13)	C_{LOAD} = 1 nF, 10% to 90% of HO Change	–	10	–	ns
t_{FALL}	Fall Time (see Figure 3) (Note 13)	C_{LOAD} = 1 nF, 90% to 10% of HO Change	–	15	–	ns
t_{LEB}	DESAT Leading Edge Blanking Time (See Figure 6)		200	450	700	ns
t_{FILTER}	DESAT Threshold Filtering Time (see Figure 6)		–	320	600	ns
t_{STO}	Soft Turn Off Time (see Figure 6)	C_{LOAD} = 10 nF, R_G = 10 Ω	1.2	1.8	3	μs
t_{FLT}	Delay after t_{FILTER} to $\overline{FLT}$ Low		100	450	700	ns
t_{FLT1}	Delay from $V_{UVLO1-OUT-OFF}$ Triggered to $\overline{FLT}$ Low		–	1.5	–	μs
t_{FLT2}	Delay from t_{UVF2} to $\overline{FLT}$ Low		–	2.4	–	μs
t_{MUTE}	IN Mute Time after t_{FILTER}, or UVLO1, UVLO2 Triggered		20	–	–	μs
t_{UVR1}	Delay from $V_{UVLO1-OUT-ON}$ Triggered to HO High	(Note 13)	–	770	–	ns
t_{UVF1}	Delay from $V_{UVLO1-OUT-OFF}$ Triggered to HO Low	(Note 13)	–	1500	–	ns
t_{UVR2}	Delay from $V_{UVLO2-OUT-ON}$ Triggered to HO High	(Note 13)	–	1000	–	ns
t_{UVF2}	Delay from $V_{UVLO2-OUT-OFF}$ Triggered to HO Low (see Figure 5)	(Note 13)	–	1000	–	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
12. Table values are valid for 3.3 V and 5 V V_{DD}, for higher V_{DD} voltages, the threshold values are maintained at the 5 V V_{DD} levels.
13. Values based on design and/or characterization.

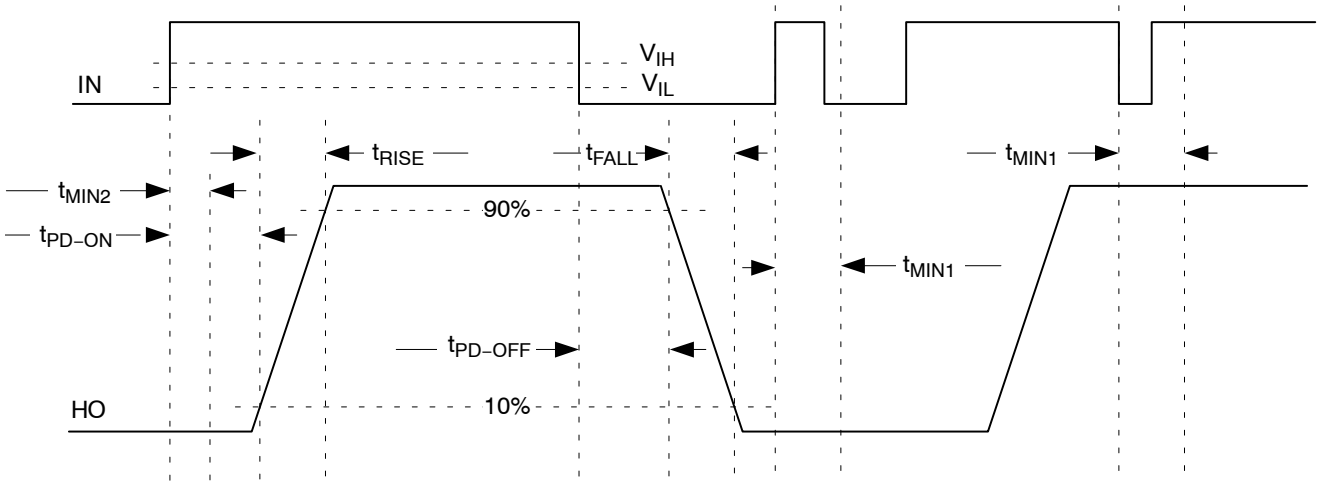


Figure 3. Propagation Delay, Rise and Fall Time

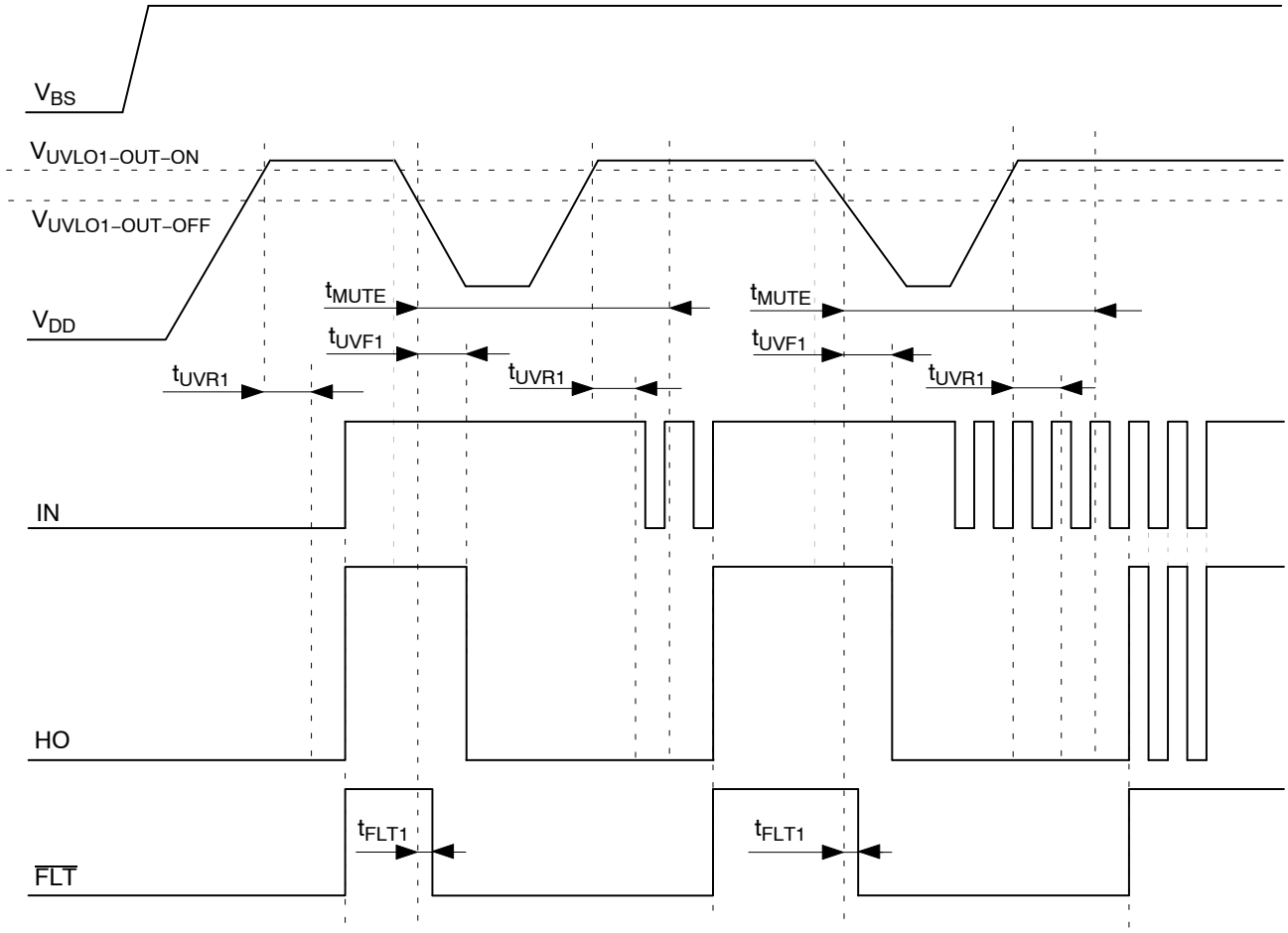


Figure 4. UVLO1 Waveform

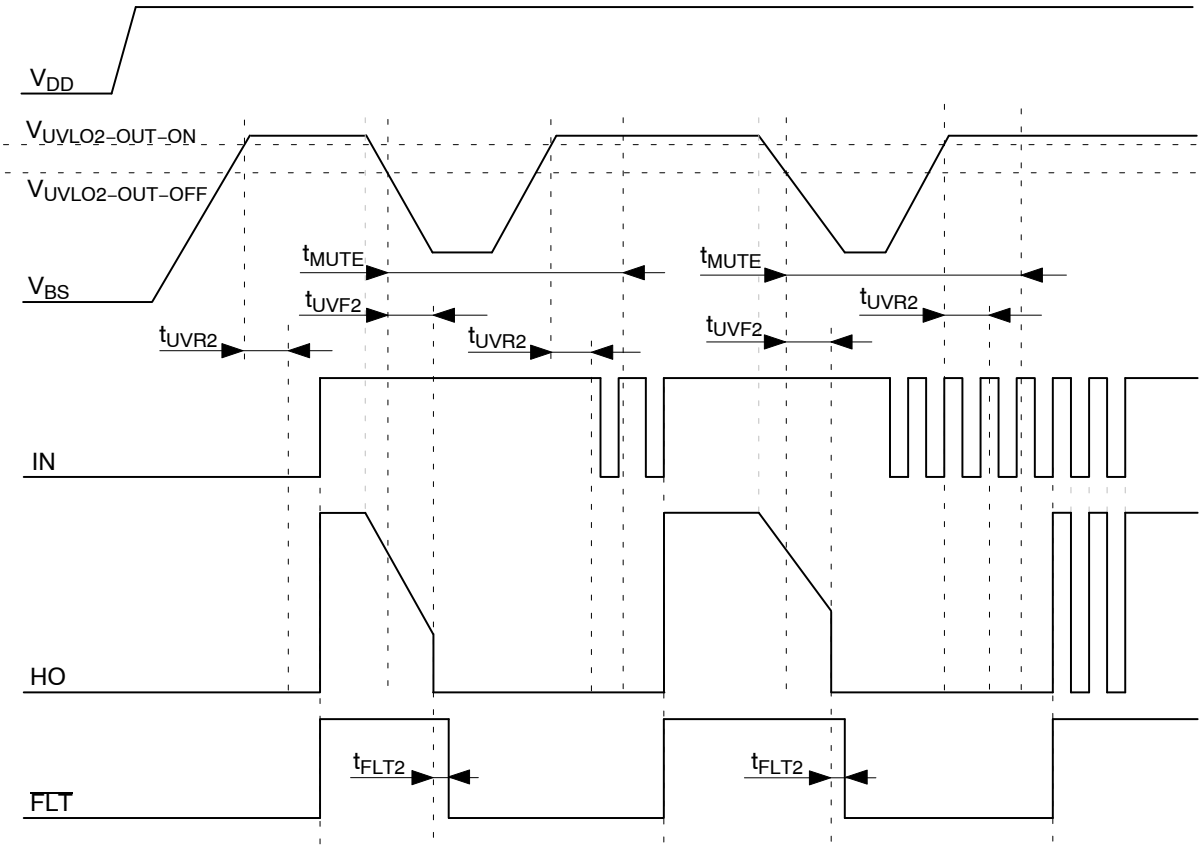


Figure 5. UVLO2 Waveform

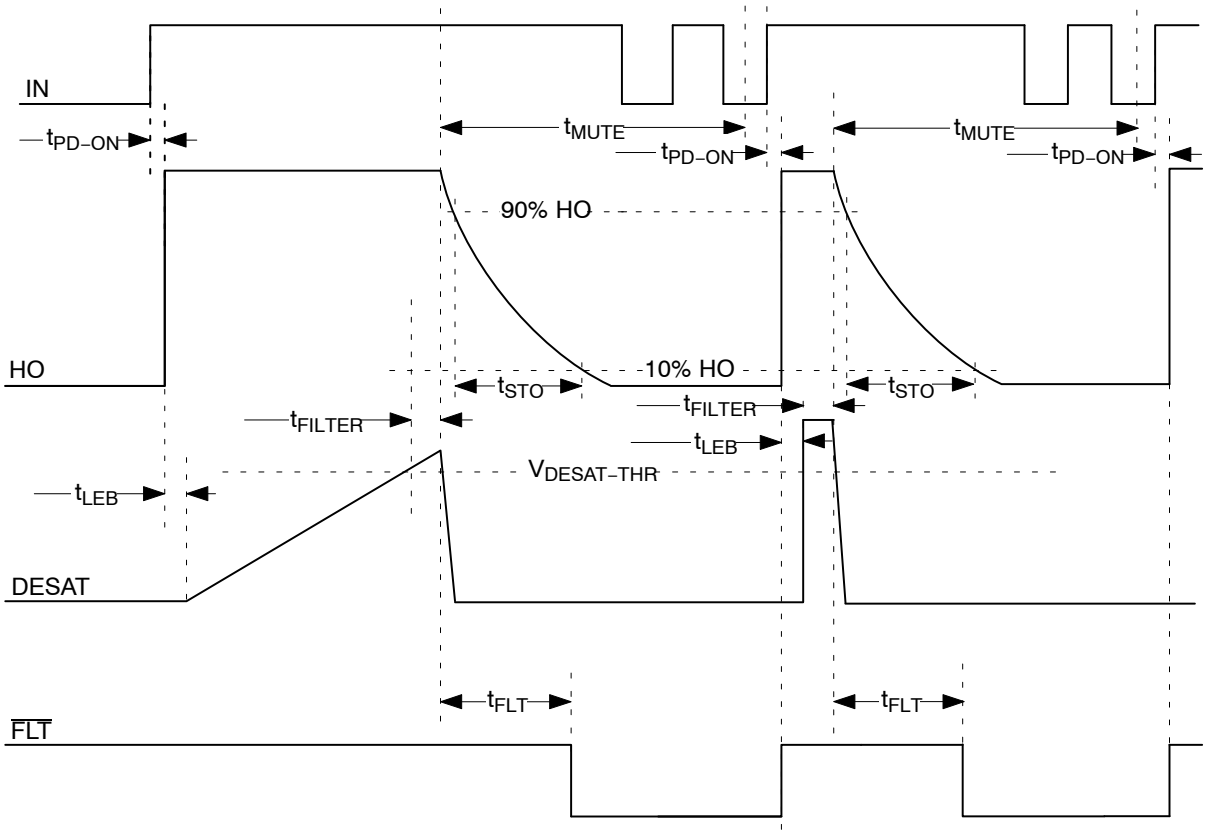


Figure 6. DESAT Response Waveform

TRUTH TABLE

IN	UVLO1	UVLO2	DESAT	HO	$\overline{FLT}$	Notes
L	Inactive	Inactive	L	L	L	Initial condition after power up V_{DD} and V_{BS}
↗	Inactive	Inactive	L	↗	↗	Initial condition – IN First Rising edge
H	Inactive	Inactive	L	H	H	Normal Operation – Output High
↘	Inactive	Inactive	L	↘	H	Normal Operation – Turn off Output
L	Inactive	Inactive	L	L	H	Normal Operation – Output Low
X	Active	Inactive	X	L	L	UVLO1 Activated – FLT Low (t_{FLT1}), Output Low
↗	Inactive	Inactive	L	↗	↗	FLT reset, UVLO1 conditions disappear
X	Inactive	Active	X	L	L	UVLO2 Activated – FLT Low (t_{FLT1}), Output Low
↗	Inactive	Inactive	L	↗	↗	FLT reset, UVLO2 conditions disappear
H	Inactive	Inactive	H (>t_{FILTER})	L	L	DESAT Activated – FLT Low (t_{FLT}), Output Low
↗	Inactive	Inactive	L	↗	↗	FLT reset, DESAT conditions disappear

ORDERING INFORMATION

Device	Package	Shipping†
NCD57084DR2G	SOIC−8 Narrow Body, (Pb−Free)	2500 / Tape & Reel
NCV57084DR2G	SOIC−8 Narrow Body, (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

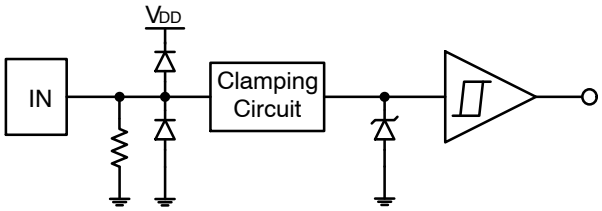


Figure 7. Input Pin Structure

TYPICAL CHARACTERISTICS

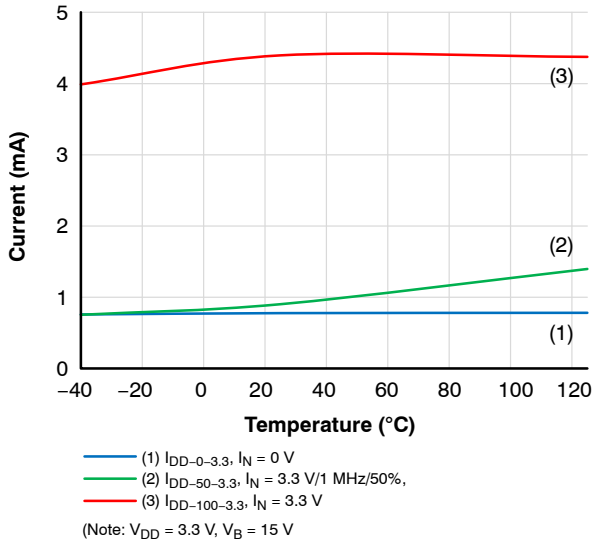


Figure 8. I_{DD} Supply Current, V_{DD} = 3.3 V

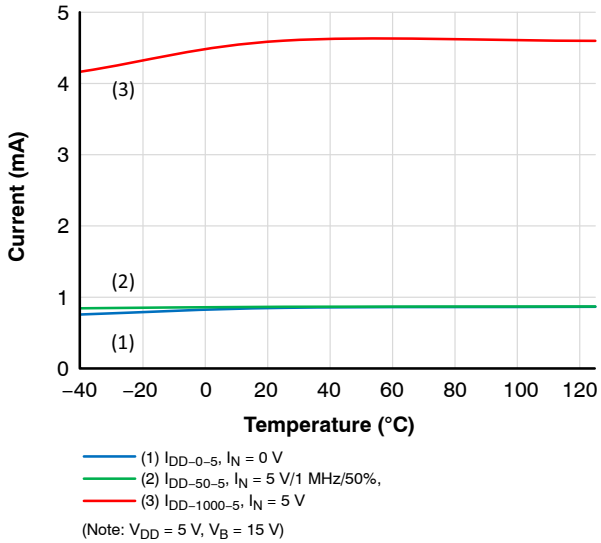


Figure 9. I_{DD} Supply Current, V_{BS} = 5 V

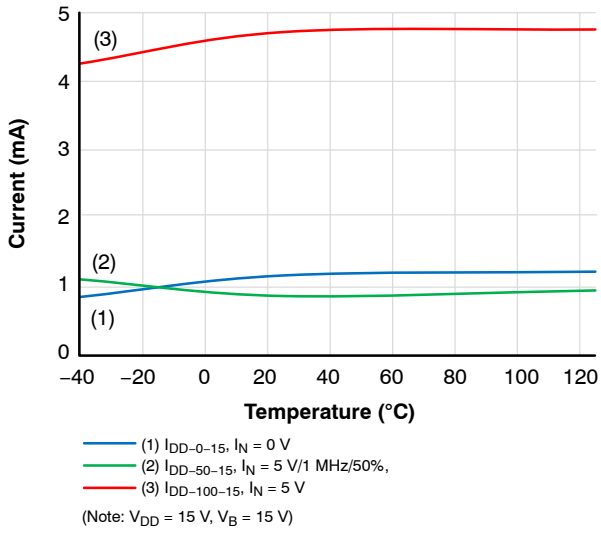


Figure 10. I_{DD} Supply Current, V_{DD} = 15 V

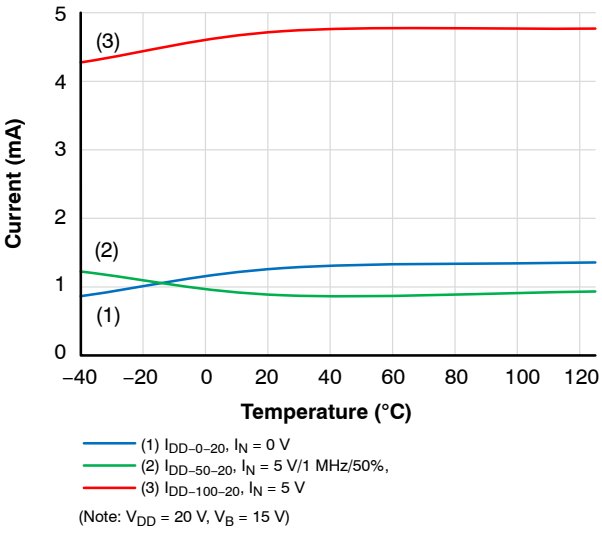


Figure 11. I_{DD} Supply Current, V_{DD} = 20 V

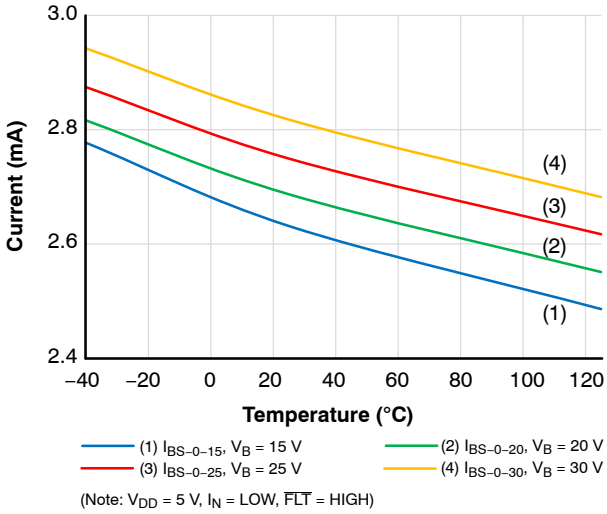


Figure 12. I_{BS} Supply Current, V_{DD} = 5 V

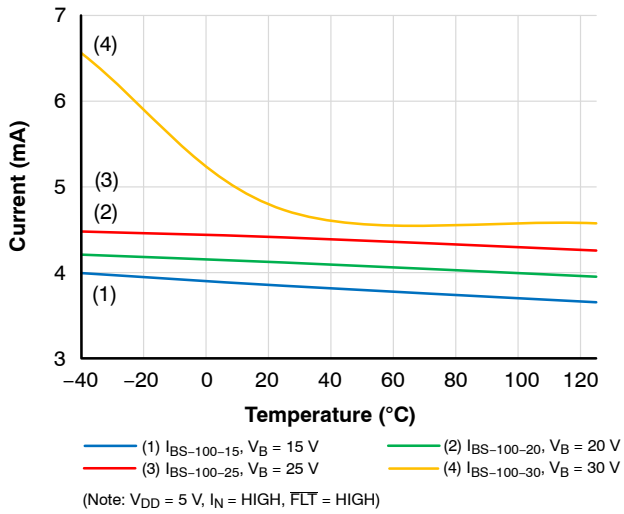
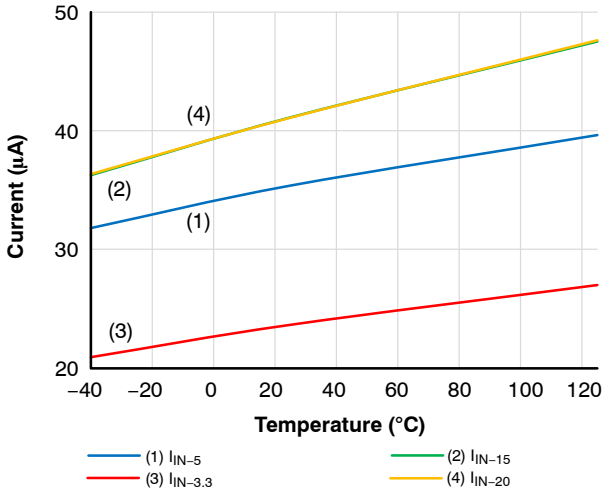
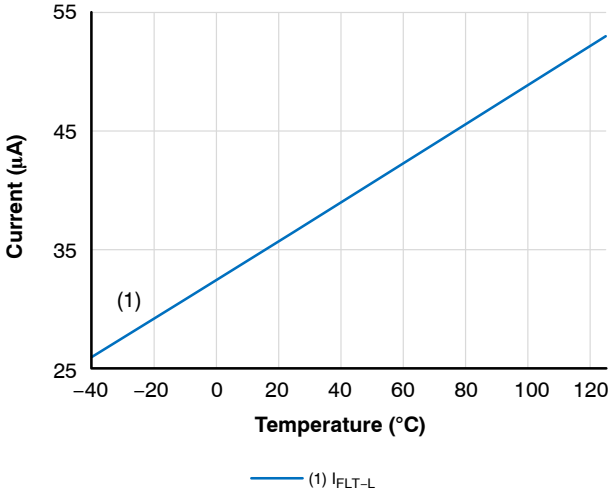


Figure 13. I_{BS} Supply Current, V_{DD} = 5 V



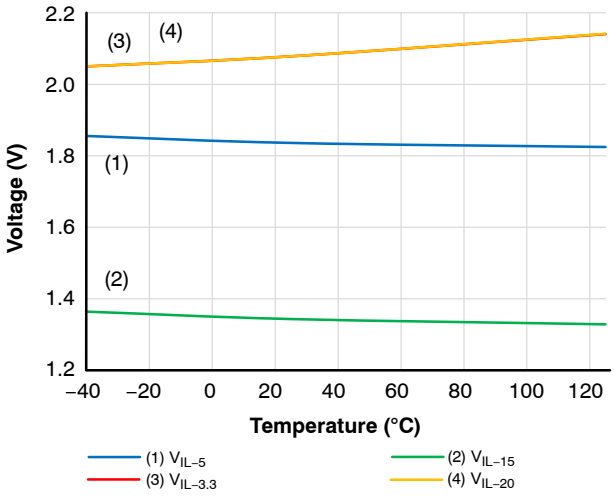
(Note: V_{IN} = V_{DD}, V_{BS} = 15 V)

Figure 14. Input Current − Logic “1”



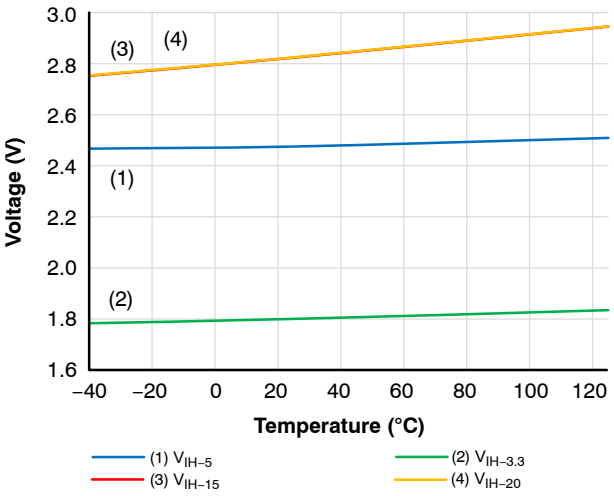
(Note: FLT = LOW, V_{DD} = 5 V)

Figure 15. FLT = Pull−up Current



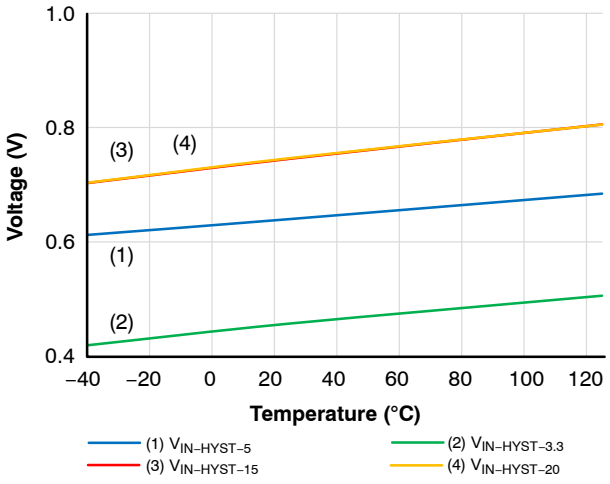
(Note: V_{BS} = 15 V)

Figure 16. Low Input Voltage



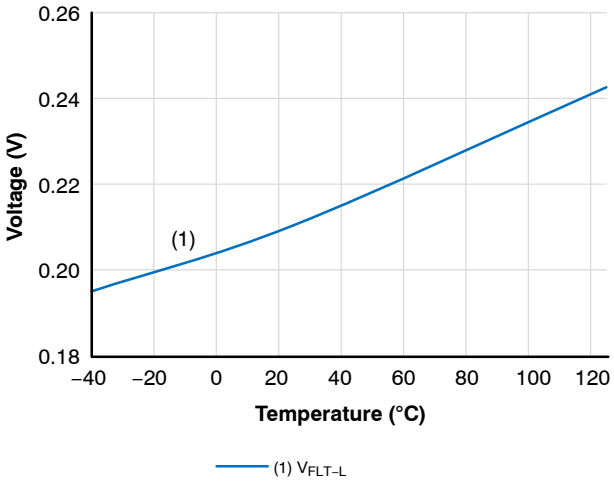
(Note: V_{BS} = 15 V)

Figure 17. High Input Voltage



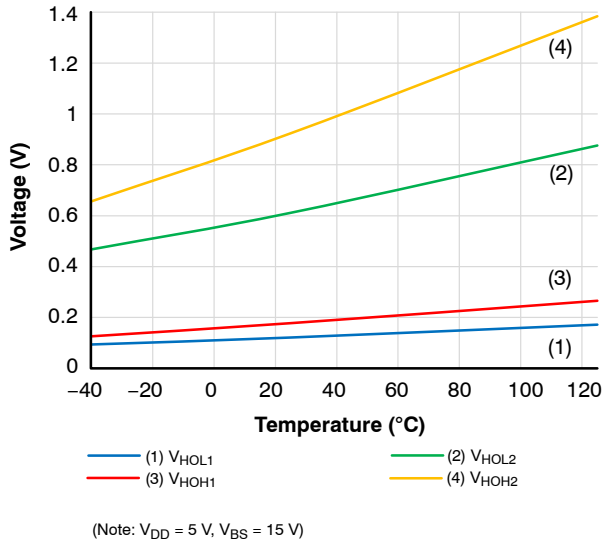
(Note: V_{BS} = 15 V)

Figure 18. Input Hysteresis Voltage



(Note: I_{FLT} = 5 mA)

Figure 19. FLT Low Level Output Voltage



(Note: V_{DD} = 5 V, V_{BS} = 15 V)

Figure 20. Output Voltage

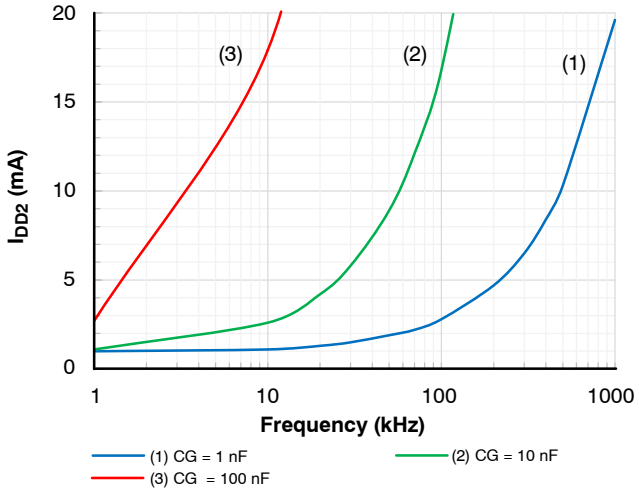


Figure 21. I_{BS} vs Switching Frequency

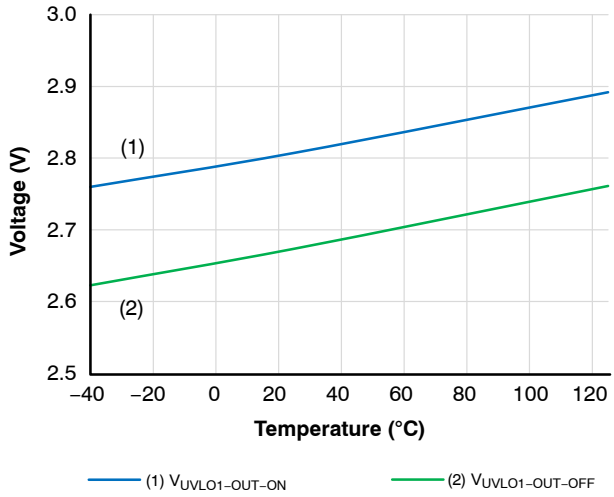


Figure 22. UVLO1 Threshold Voltage

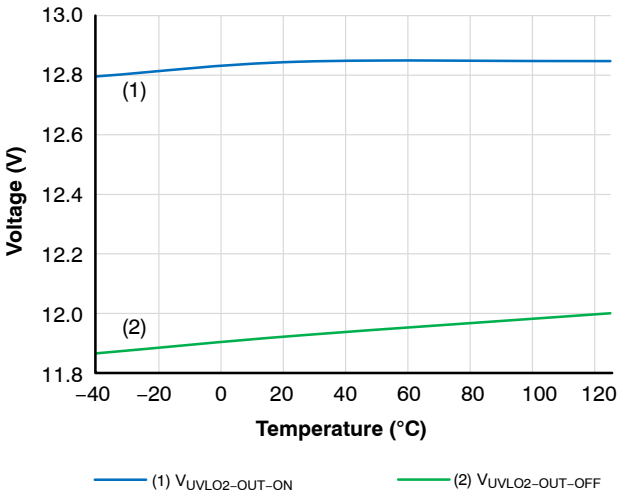


Figure 23. UVLO2 Threshold Voltage

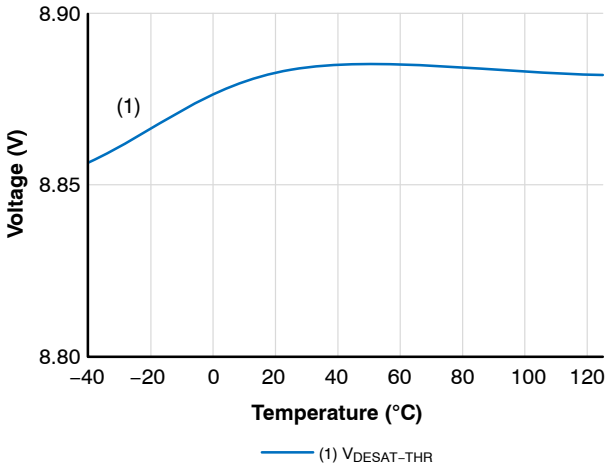


Figure 24. DESAT Threshold Voltage

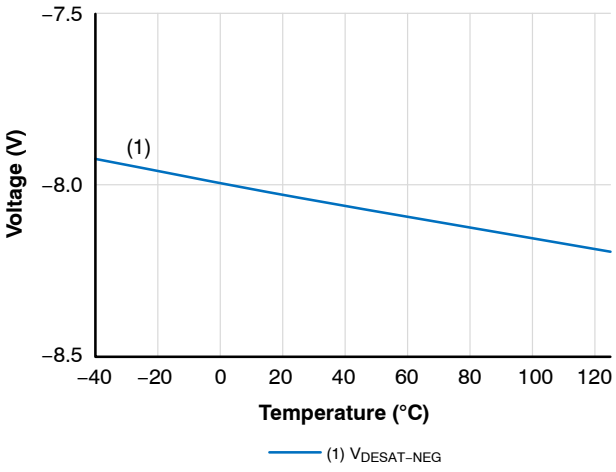


Figure 25. DESAT Negative Voltage

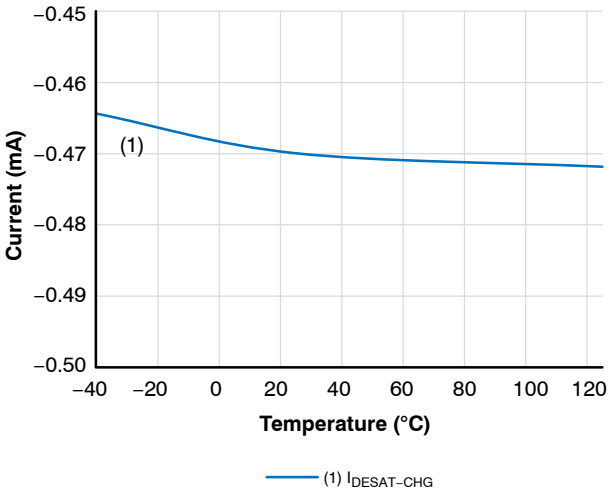


Figure 26. DESAT Blanking Charge Current

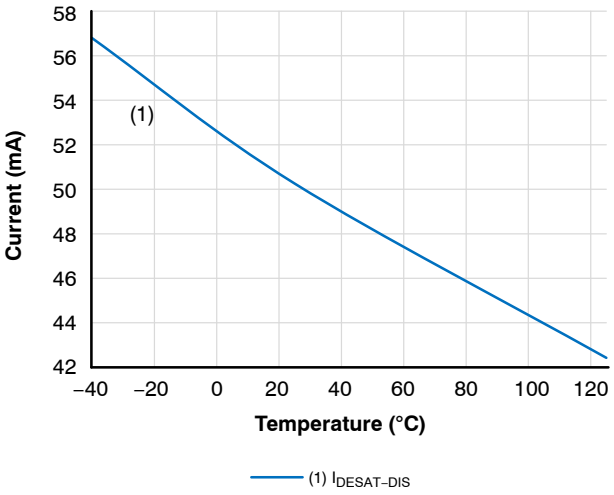


Figure 27. DESAT Blanking Discharge Current

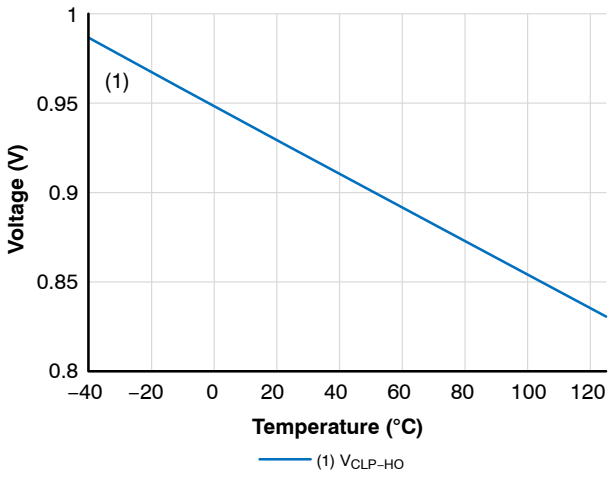
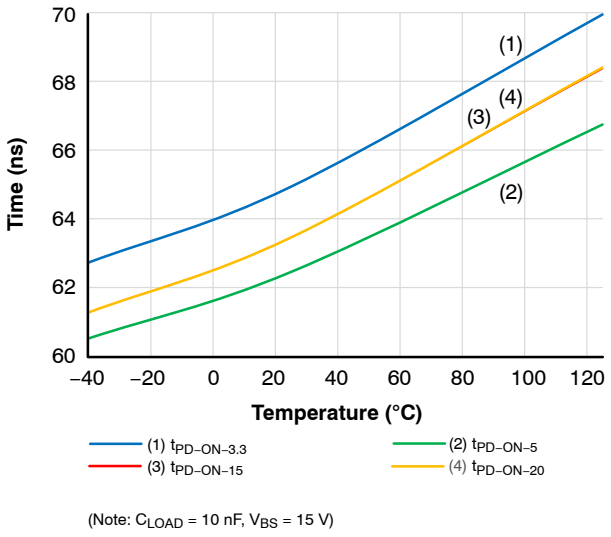
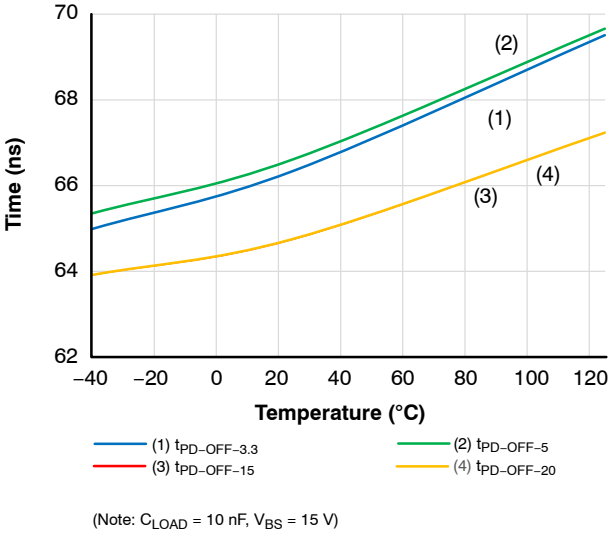


Figure 28. IGBT Short Circuit Clamping Voltage



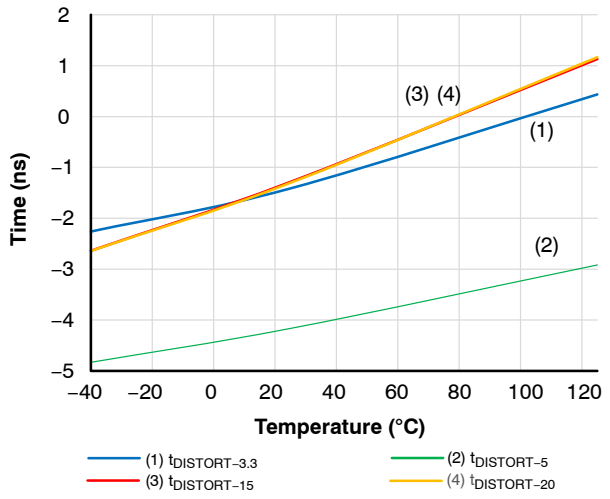
(Note: C_{LOAD} = 10 nF, V_{BS} = 15 V)

Figure 29. High Propagation Delay



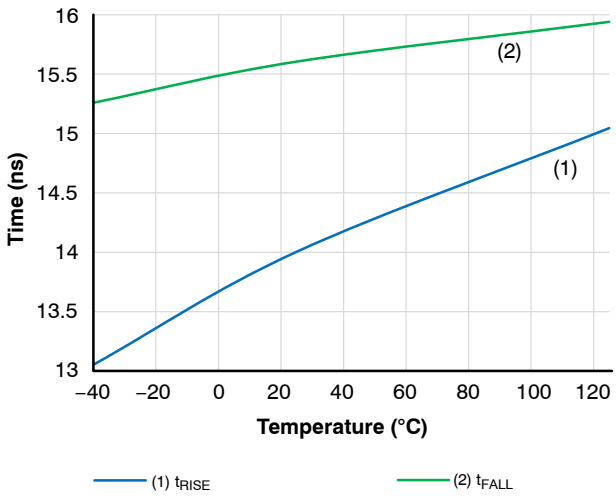
(Note: C_{LOAD} = 10 nF, V_{BS} = 15 V)

Figure 30. Low Propagation Delay



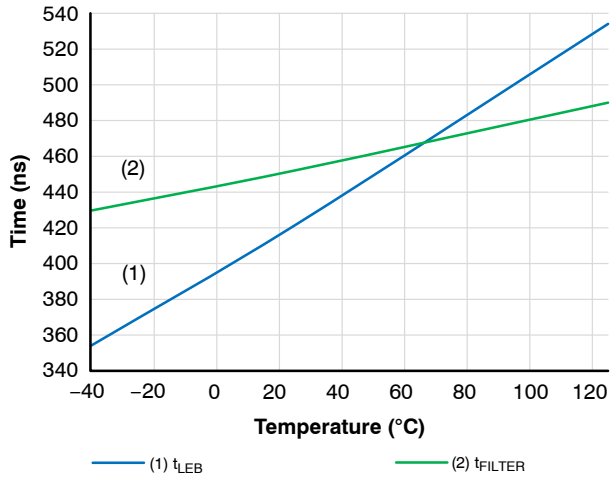
(Note: V_{BS} = 15 V)

Figure 31. Propagation Delay Distortion



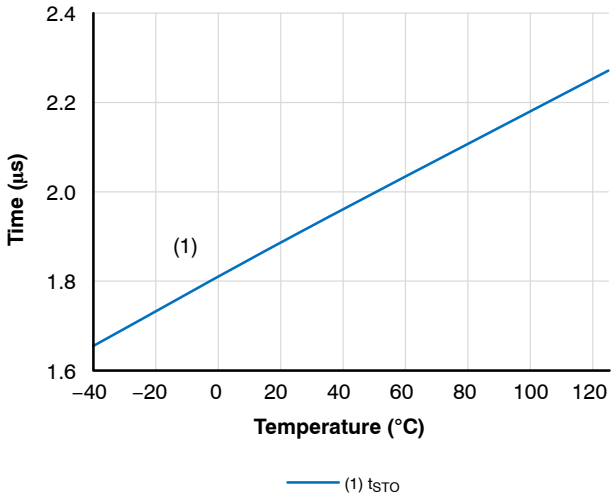
(Note: C_{LOAD} = 1 nF, V_{BS} = 15 V)

Figure 32. Rise / Fall Time



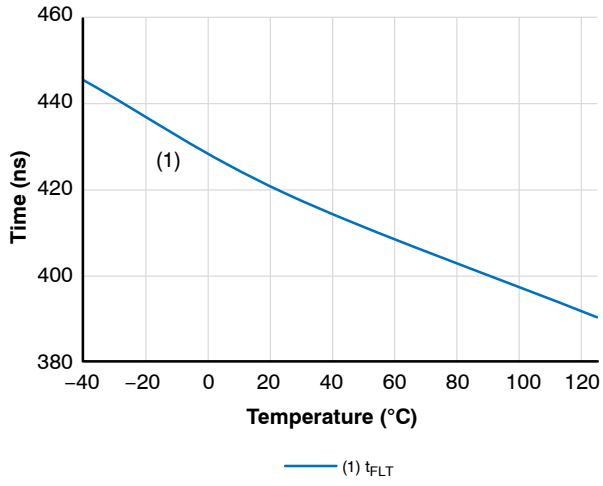
(Note: V_{DD} = 5 V, V_{BS} = 15 V)

Figure 33. DESAT Threshold Filtering Time, DESAT Leading Edge Blanking Time



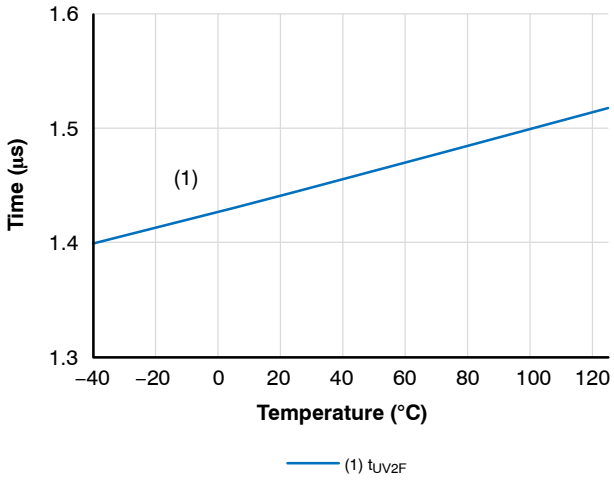
(Note: V_{DD} = 5 V, V_{BS} = 15 V)

Figure 34. Soft Turn Off Time



(Note: V_{DD} = 5 V, V_{BS} = 15 V)

Figure 35. FLT Delay Time



(Note: V_{DD} = 5 V, V_{BS} falls from HI to LOW)

Figure 36. UVLO2 Fall Delay

Under Voltage Lockout (UVLO)

UVLO ensures correct switching of IGBT connected to the driver output.

- The IGBT is turned−off and the output is disabled, if the supply V_{DD} drops below $V_{UVLO1-OUT-OFF}$ or V_{BS} drops below $V_{UVLO2-OUT-OFF}$.
- The driver output does not follow the input signal on V_{IN} until the V_{DD} / V_{BS} rises above the $V_{UVLOX-OUT-ON}$ and the input signal rising edge is applied to the V_{IN}.

With high loading gate capacitances over 10 nF it is important to follow the decoupling capacitor routing guidelines as shown on Figure 37. The decoupling capacitor value should be at least 10 μF. Also gate resistor of minimal value of 2 Ω has to be used in order to avoid interference of the high di/dt with internal circuitry (e.g. UVLO2).

After the power-on of the driver there has to be a rising edge applied to the IN in order for the output to start following the inputs. This serves as a protection against producing partial pulses at the output if the V_{DD} or V_B is applied in the middle of the input PWM pulse.

Power Supply (V_{DD}, V_{BS})

NCx57084 is designed to support unipolar power supply.

For reliable high output current the suitable external power capacitors required. Parallel combination of 100 nF + 4,7 μF ceramic capacitors is optimal for a wide range of applications using IGBT. For reliable driving IGBT modules (containing several parallel IGBT´s) a higher capacity required (typically 100 nF + 10 μF). Capacitors should be as close as possible to the driver's power pins.

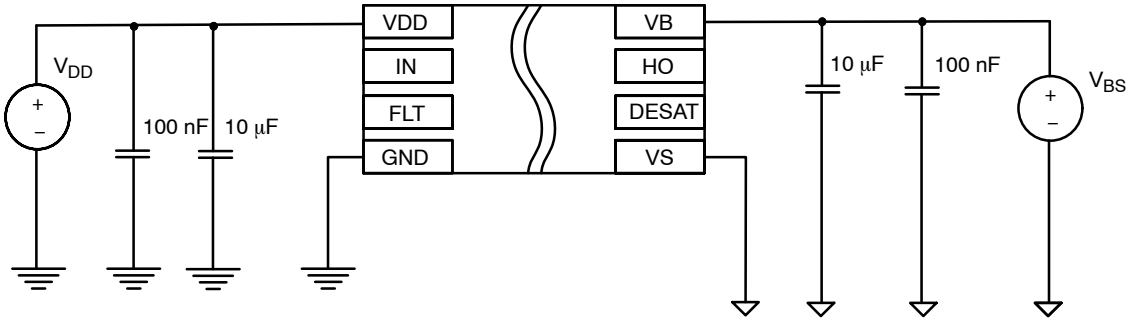


Figure 37. Power Supply

Desaturation Protection (DESAT)

Desaturation protection ensures the protection of IGBT at short circuit. When the V_{CESAT} voltage goes up and reaches the set limit, the output is driven low and $\overline{FLT}$ output is activated. Blanking time can be set by internal current source and an external capacitor. To avoid false DESAT triggering and minimize blanking time, fast switching diodes with low internal capacitance are recommended. All DESAT protective diodes internal capacitances builds voltage divider with the blanking capacitor.

Warning: Both external protective diodes are recommended for the protection against voltage spikes caused by IGBT transients passing through parasitic capacitances.

$$t_{BLANK} = C_{BLANK} \cdot \frac{V_{DESAT-THR}}{I_{DESAT-CHG}}$$

$$V_{DESAT-THR} > R_{S-DESAT} \cdot I_{DESAT-CHG} + V_{F\ HV\ diode} + V_{CESAT\_IGBT}$$

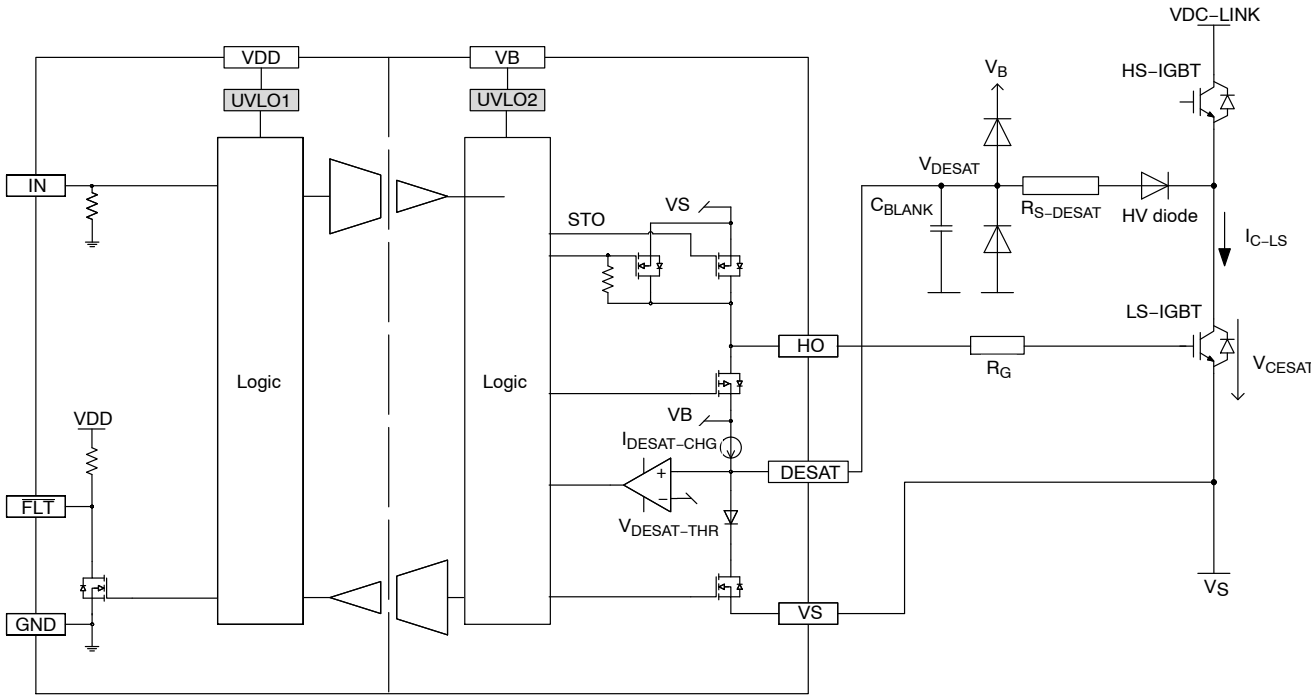
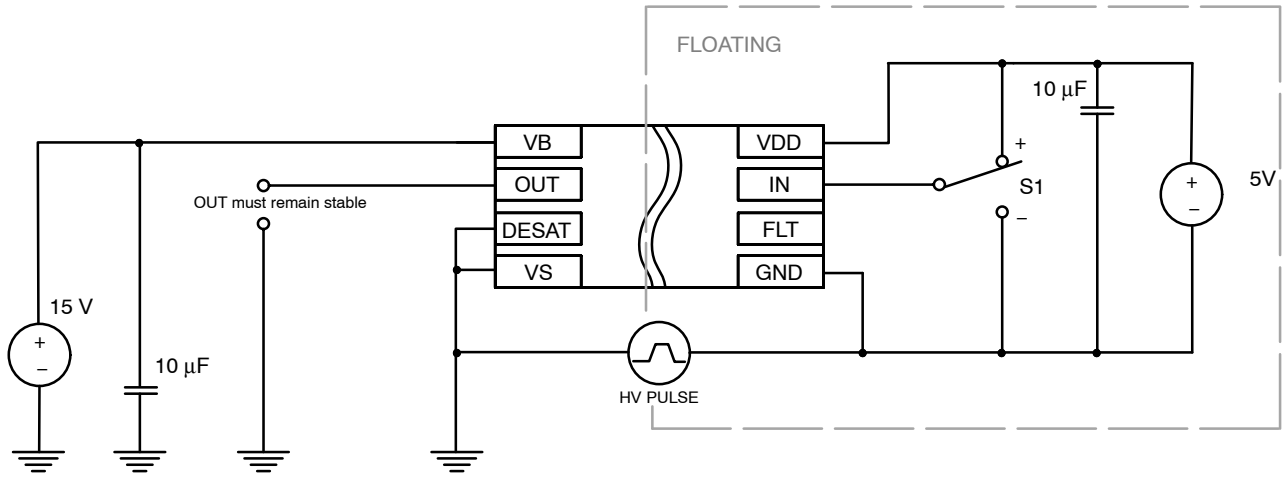


Figure 38. DESAT Circuit Parameters Specification



(Test Conditions: HV Pulse ±1500 V, dV/dt = 1−100 V/ns, V_{DD} = 5 V, V_{BS} = 15 V)

Figure 39. CMTI Test Setup

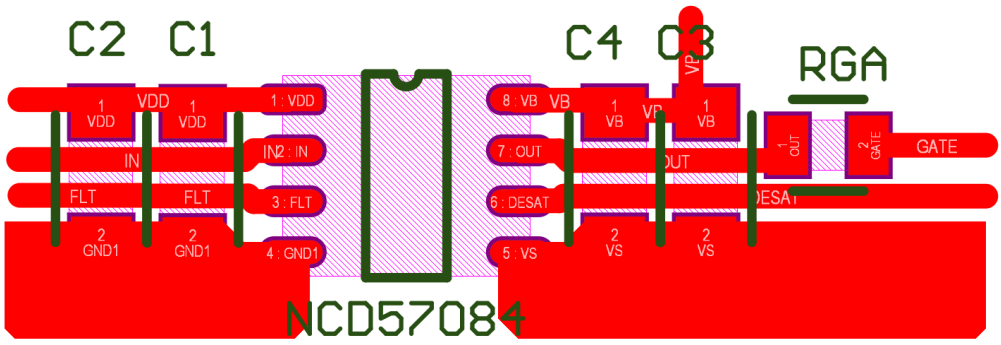


Figure 40. Recommended Layout

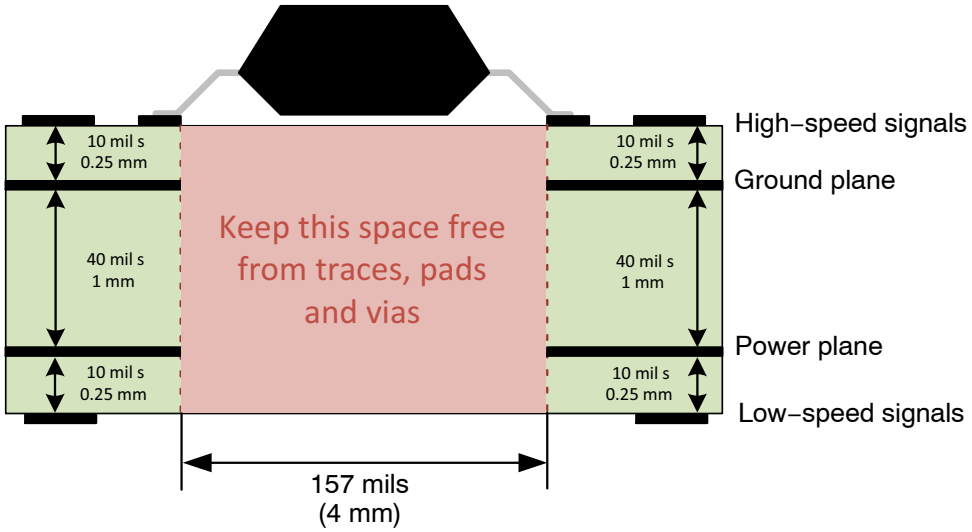
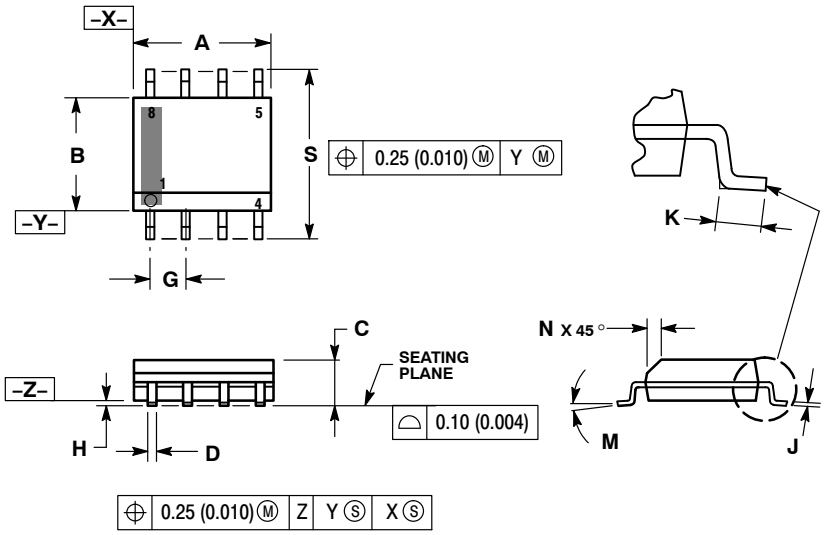


Figure 41. Recommended Layer Stack

PACKAGE DIMENSIONS

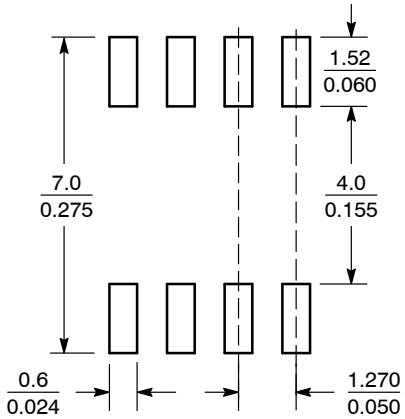
SOIC−8 NB
CASE 751−07
ISSUE AK



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

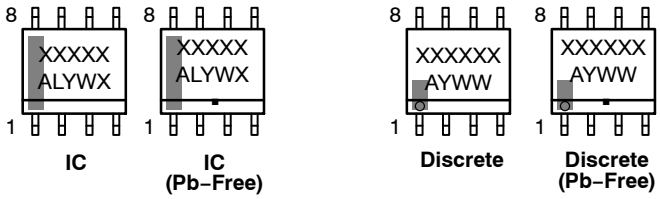
SOLDERING FOOTPRINT*



SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊